Thorsten Schultz

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/2559574/publications.pdf

Version: 2024-02-01

40	1,484	393982	315357
papers	citations	19 h-index	38 g-index

41	41	41	2614
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Atomic Layer Deposition of MoS₂ Decorated TiO₂ Nanotubes for Photoelectrochemical Water Splitting. Advanced Materials Interfaces, 2022, 9, .	1.9	8
2	The Interlayer Method: A Universal Tool for Energy Level Alignment Tuning at Inorganic/Organic Semiconductor Heterojunctions. Advanced Functional Materials, 2021, 31, 2010174.	7.8	18
3	The energy level alignment of the ferroceneâ€“EGaIn interface studied with photoelectron spectroscopy. Physical Chemistry Chemical Physics, 2021, 23, 13458-13467.	1.3	5
4	Disentangling Bulk and Interface Phenomena in a Molecularly Doped Polymer Semiconductor. Advanced Optical Materials, 2021, 9, 2002039.	3.6	6
5	Tuning material properties of amorphous zinc oxynitride thin films by magnesium addition. APL Materials, 2021, 9, 021120.	2.2	2
6	Typeâ€I Energy Level Alignment at the PTCDAâ€”Monolayer MoS₂ Interface Promotes Resonance Energy Transfer and Luminescence Enhancement. Advanced Science, 2021, 8, 2100215.	5.6	19
7	Temperatureâ€Dependent Electronic Groundâ€State Charge Transfer in van der Waals Heterostructures. Advanced Materials, 2021, 33, e2008677.	11.1	12
8	Two-dimensional plasmonic polarons in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math> -doped monolayer <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow><mml:mi>MoS</mml:mi></mml:mrow><mml:mn>2</mml:mn></mml:msub></mml:math> . Physical Review B, 2021, 103, .	1.1	13
9	Energy Level Alignment at the C₆₀/Monolayerâ€WS₂ Interface on Insulating and Conductive Substrates. Advanced Electronic Materials, 2021, 7, 2100425.	2.6	6
10	The Schottkyâ€“Mott Rule Expanded for Two-Dimensional Semiconductors: Influence of Substrate Dielectric Screening. ACS Nano, 2021, 15, 14794-14803.	7.3	25
11	Strain states and relaxation for $$alpha$$-(Al$$_x$$Ga$$_{1-x}$$)$$_2$$O$$_3$$ thin films on prismatic planes of $$alpha$$-Al$$_2$$O$$_3$$ in the full composition range: Fundamental difference of a- and m-epitaxial planes in the manifestation of shear strain and lattice tilt. Journal of Materials Research, 2021, 36, 4816-4831.	1.2	9
12	Benzocyclobutene polymer as an additive for a benzocyclobutene-fullerene: application in stable pâ€“iâ€“n perovskite solar cells. Journal of Materials Chemistry A, 2021, 9, 9347-9353.	5.2	6
13	Morphology-controlled MoS₂ by low-temperature atomic layer deposition. Nanoscale, 2020, 12, 20404-20412.	2.8	14
14	Thermally Activated Goldâ€Mediated Transition Metal Dichalcogenide Exfoliation and a Unique Goldâ€Mediated Transfer. Physica Status Solidi - Rapid Research Letters, 2020, 14, 2000408.	1.2	25
15	Conductive Polymer Work Function Changes due to Residual Water: Impact of Temperatureâ€Dependent Dielectric Constant. Advanced Electronic Materials, 2020, 6, 2000408.	2.6	12
16	Position-locking of volatile reaction products by atmosphere and capping layers slows down photodecomposition of methylammonium lead triiodide perovskite. RSC Advances, 2020, 10, 17534-17542.	1.7	16
17	The optical signatures of molecular-doping induced polarons in poly(3-hexylthiophene-2,5-diyl): individual polymer chainsversusaggregates. Journal of Materials Chemistry C, 2020, 8, 2870-2879.	2.7	32
18	Solubility limit and material properties of a Î²-(AlxGa1â^'x)2O3 thin film with a lateral cation gradient on (00.1)Al2O3 by tin-assisted PLD. APL Materials, 2020, 8, 021103.	2.2	26

#	Article	IF	Citations
19	Excited-State Charge Transfer Enabling MoS₂/Phthalocyanine Photodetectors with Extended Spectral Sensitivity. Journal of Physical Chemistry C, 2020, 124, 2837-2843.	1.5	30
20	Band Offsets at Î²-([Al,In]_xGa_{1â€“x})₂O₃/MgO Interfaces. ACS Applied Materials & Interfaces, 2020, 12, 8879-8885.	4.0	14
21	Growth of Nb-Doped Monolayer WS₂ by Liquid-Phase Precursor Mixing. ACS Nano, 2019, 13, 10768-10775.	7.3	102
22	Demonstration of the key substrate-dependent charge transfer mechanisms between monolayer MoS2 and molecular dopants. Communications Physics, 2019, 2, .	2.0	38
23	Electronic band dispersion determination in azimuthally disordered transition-metal dichalcogenide monolayers. Communications Physics, 2019, 2, .	2.0	11
24	Direct observation of state-filling at hybrid tin oxide/organic interfaces. Applied Physics Letters, 2019, 114, .	1.5	4
25	Modulation of the Work Function by the Atomic Structure of Strong Organic Electron Acceptors on Hâ€Si(111). Advanced Electronic Materials, 2019, 5, 1800891.	2.6	30
26	Surface Termination Dependent Work Function and Electronic Properties of Ti₃C₂T_x MXene. Chemistry of Materials, 2019, 31, 6590-6597.	3.2	359
27	Epitaxial Î²-(AlxGa1â^’x)2O3 thin films and heterostructures grown by tin-assisted VCCS-PLD. APL Materials, 2019, 7, .	2.2	30
28	Importance of Substrate Work Function Homogeneity for Reliable Ionization Energy Determination by Photoelectron Spectroscopy. Physica Status Solidi (B): Basic Research, 2019, 256, 1800299.	0.7	18
29	Tin-assisted heteroepitaxial PLD-growth of Î²-Ga2O3 thin films with high crystalline quality. APL Materials, 2019, 7, .	2.2	98
30	Electronic properties of hybrid organic/inorganic semiconductor pn-junctions. Journal of Physics Condensed Matter, 2019, 31, 064002.	0.7	16
31	Direct determination of monolayer MoS₂and WSe₂exciton binding energies on insulating and metallic substrates. 2D Materials, 2018, 5, 025003.	2.0	142
32	Influence of Oxygen Deficiency on the Rectifying Behavior of Transparent-Semiconducting-Oxideâ€“Metal Interfaces. Physical Review Applied, 2018, 9, .	1.5	29
33	Impact of surface states and bulk doping level on hybrid inorganic/organic semiconductor interface energy levels. Journal of Applied Physics, 2018, 123, 245501.	1.1	22
34	A Multifunctional Interlayer for Solution Processed High Performance Indium Oxide Transistors. Scientific Reports, 2018, 8, 10946.	1.6	23
35	Microstructure and Elastic Constants of Transition Metal Dichalcogenide Monolayers from Friction and Shear Force Microscopy. Advanced Materials, 2018, 30, e1803748.	11.1	16
36	Reliable Work Function Determination of Multicomponent Surfaces and Interfaces: The Role of Electrostatic Potentials in Ultraviolet Photoelectron Spectroscopy. Advanced Materials Interfaces, 2017, 4, 1700324.	1.9	61

#	Article	IF	Citations
37	Electronic Properties of a 1D Intrinsic/p-Doped Heterojunction in a 2D Transition Metal Dichalcogenide Semiconductor. ACS Nano, 2017, 11, 9128-9135.	7.3	58
38	Surface State Density Determines the Energy Level Alignment at Hybrid Perovskite/Electron Acceptors Interfaces. ACS Applied Materials & Interfaces, 2017, 9, 41546-41552.	4.0	89
39	Energy level tuning at inorganic/organic semiconductor heterojunctions. , 2016, , .		0
40	Tuning the work function of GaN with organic molecular acceptors. Physical Review B, 2016, 93, .	1.1	40